

Black Lithium Niobate

Process solutions

Key benefits

- ✓ Pyro-electric effect removal by thermal treatment under vacuum
 - Generation of oxygen vacancies in the crystal
 - Prevent the device destruction by static electricity
 - No difference at the piezo-electricity property
 - Process compatible with large thermal gradient or exothermic chemical cleaning
- ✓ Fast process with no added reducing gas
- ✓ Level of reduction and the optical absorption function of the annealing temperature



4" LiNbO3 wafer after RTA



Increasing annealing temperature up to 1000 °C

AS-Premium



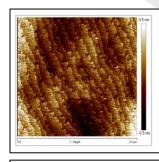
- Two sides heating furnaces with thermal compensation capability through and across wafers
- Pressure control from 0.1 to 760 Torr
- Temperature control from RT to 1300°C
- Fast heating ramp up and cooling rate (>40°C/s)
- SiC coated graphite susceptor for encapsulation of 4 and 6 inch wafers



Rapid thermal process 1200 1000 1

Conditions

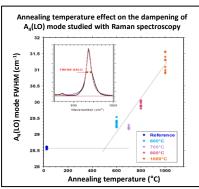
- 7°C/s heating ramp up to 1000°C
- 120s annealing stage
- Cooling until RT

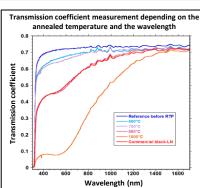


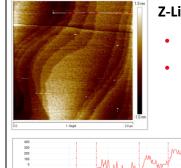
X-LiNbO3 after RTA

- **RMS** = 0.24 nm
- Terraces

 120-160 nm
 length
 20-30 Å height



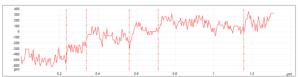




Z-LiNbO3 after RTA

- RMS = 0.31 nm
- Terraces

 140-500 nm length
 20-40 Å height



For more information contact Annealsys: contact@annealsys.com - www.annealsys.com - www.annealsys.co